

# MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

## Digital Transistors (BRT) R1 = 10 kΩ, R2 = 47 kΩ

### NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias resistor network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	6	Vdc

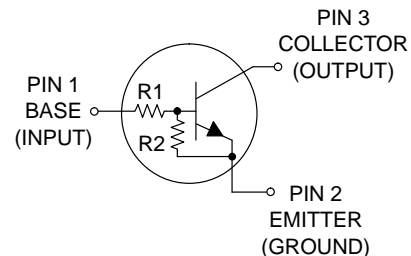
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



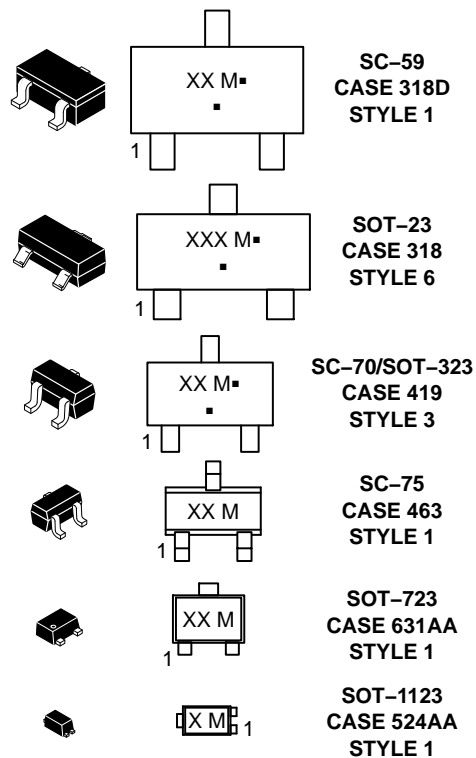
ON Semiconductor®

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#### PIN CONNECTIONS



#### MARKING DIAGRAMS



XXX = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

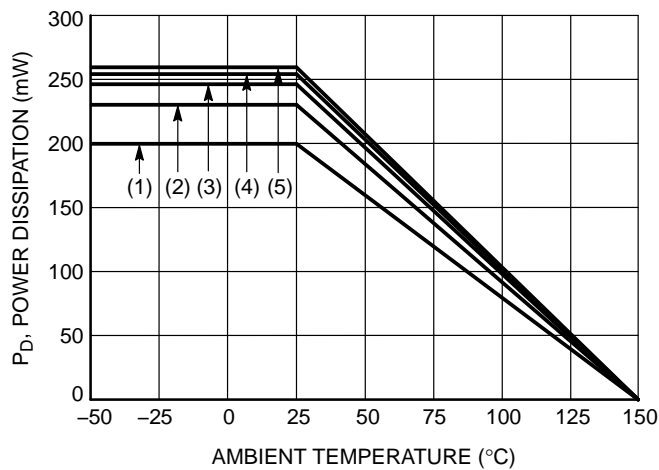
# MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

**Table 1. ORDERING INFORMATION**

Device	Part Marking	Package	Shipping†
MUN2214T1G, SMUN2214T1G*	8D	SC-59 (Pb-Free)	3000 / Tape & Reel
MUN2214T3G, SMUN2214T3G*	8D	SC-59 (Pb-Free)	10000 / Tape & Reel
MMUN2214LT1G, SMMUN2214LT1G*	A8D	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5214T1G, SMUN5214T1G*	8D	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC114YET1G, SDTC114YET1G	8D	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC114YM3T5G, NSVDTC114YM3T5G*	8D	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC114YF3T5G	J	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

**Figure 1. Derating Curve**

# MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

**Table 2. THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SC-59) (MUN2214)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	230	mW
Derate above $25^\circ\text{C}$		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-23) (MMUN2214L)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	246	mW
Derate above $25^\circ\text{C}$		2.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5214)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	202	mW
Derate above $25^\circ\text{C}$		1.6	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SC-75) (DTC114YE)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above $25^\circ\text{C}$		1.6	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
<b>THERMAL CHARACTERISTICS (SOT-723) (DTC114YM3)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$	$P_D$	260	mW
Derate above $25^\circ\text{C}$		2.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3, NSBC114YF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
<b>THERMAL CHARACTERISTICS (SOT-1123) (NSBC114YF3)</b>			
Total Device Dissipation $T_A = 25^\circ\text{C}$  Derate above $25^\circ\text{C}$	$P_D$    (Note 3) (Note 4) (Note 3) (Note 4)	254 297 2.0 2.4	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$  (Note 3) (Note 4)	493 421	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$  (Note 3)	193	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
- FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}, I_E = 0$ )	$I_{CBO}$	-	-	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}, I_B = 0$ )	$I_{CEO}$	-	-	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}, I_C = 0$ )	$I_{EBO}$	-	-	0.2	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}, I_E = 0$ )	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 5) ( $I_C = 2.0\text{ mA}, I_B = 0$ )	$V_{(BR)CEO}$	50	-	-	Vdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (Note 5) ( $I_C = 5.0\text{ mA}, V_{CE} = 10\text{ V}$ )	$h_{FE}$	80	140	-	
Collector - Emitter Saturation Voltage (Note 5) ( $I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$ )	$V_{CE(sat)}$	-	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}, I_C = 100\ \mu\text{A}$ )	$V_{i(off)}$	-	0.7	0.5	Vdc
Input Voltage (on) ( $V_{CE} = 0.3\text{ V}, I_C = 1.0\text{ mA}$ )	$V_{i(on)}$	1.4	0.8	-	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}, V_B = 2.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	-	-	Vdc
Input Resistor	$R_1$	7.0	10	13	k $\Omega$
Resistor Ratio	$R_1/R_2$	0.17	0.21	0.25	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .

TYPICAL CHARACTERISTICS  
MUN2214, MMUN2214L, MUN5214, DTC114YE, DTC114YM3

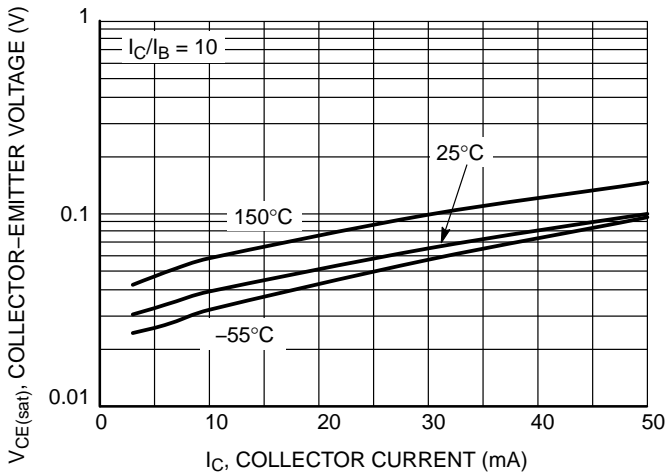


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

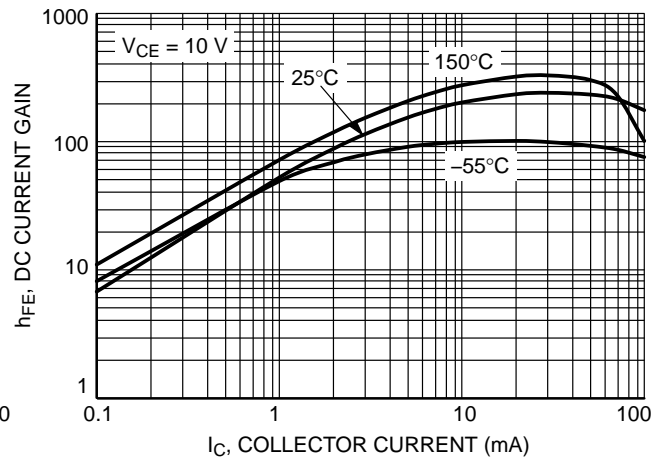


Figure 3. DC Current Gain

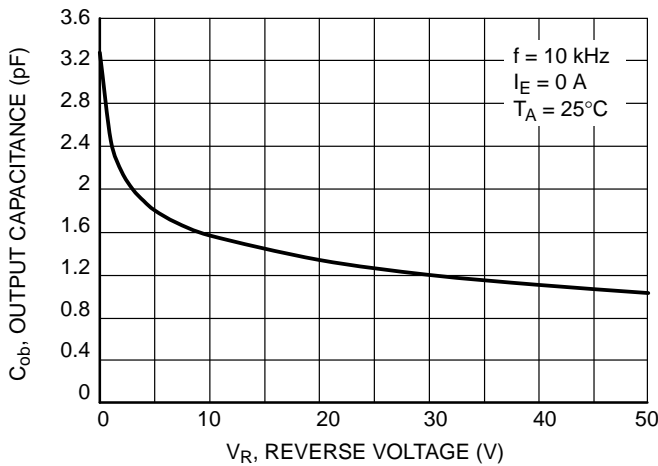


Figure 4. Output Capacitance

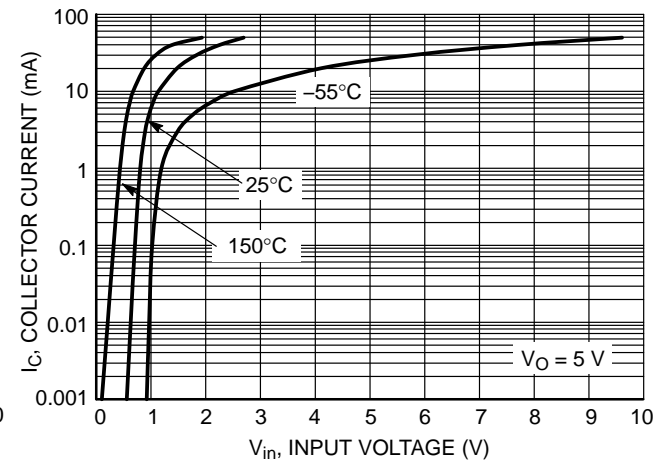


Figure 5. Output Current vs. Input Voltage

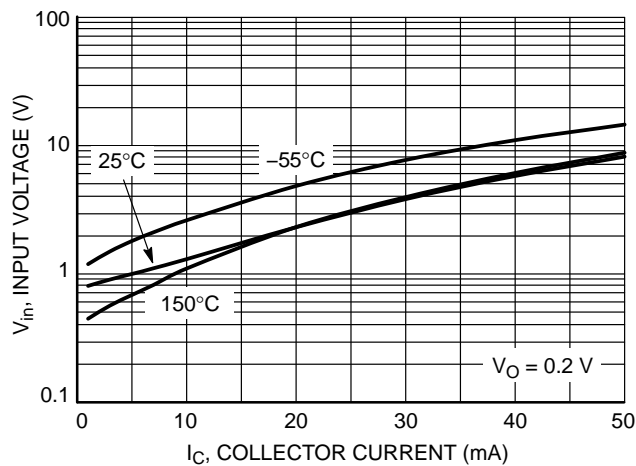


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS  
NSBC114YF3

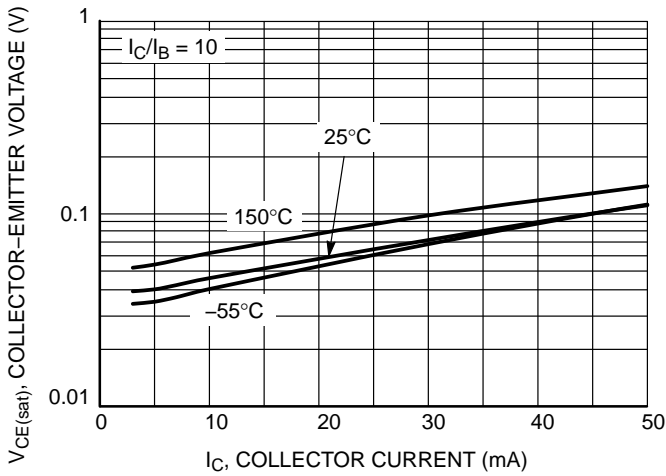


Figure 7.  $V_{CE(sat)}$  vs.  $I_C$

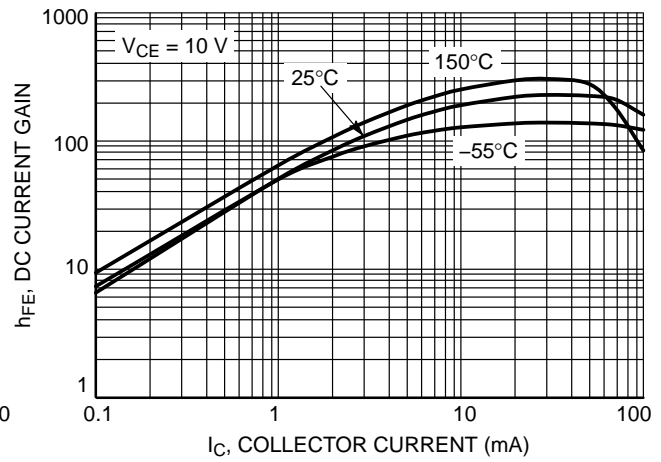


Figure 8. DC Current Gain

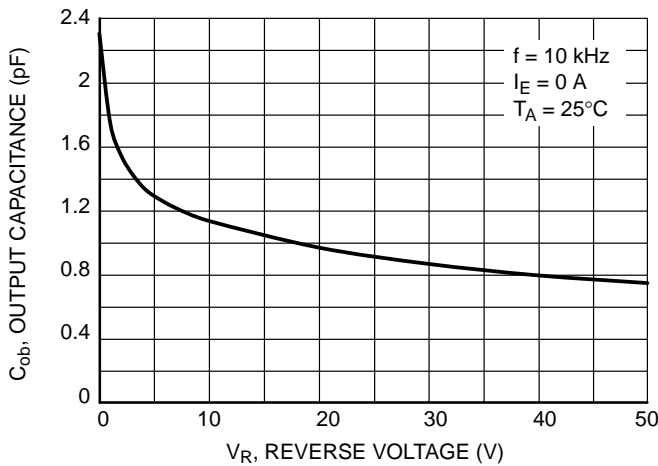


Figure 9. Output Capacitance

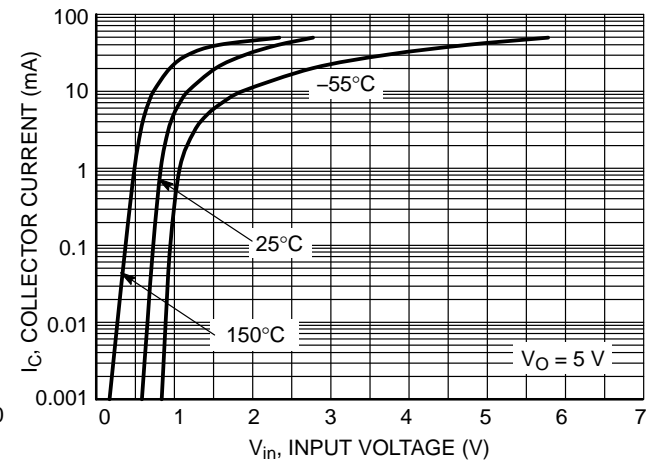


Figure 10. Output Current vs. Input Voltage

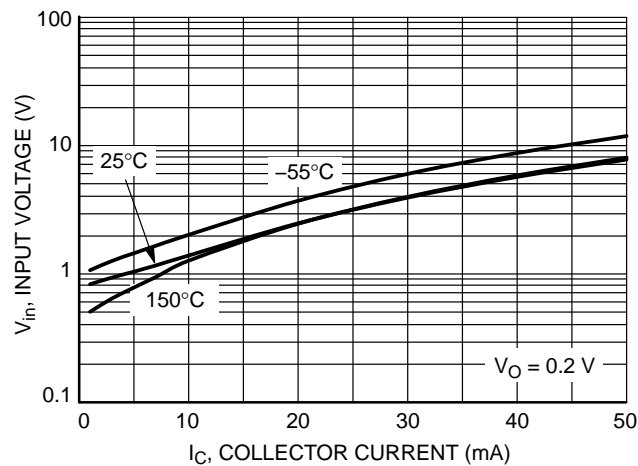
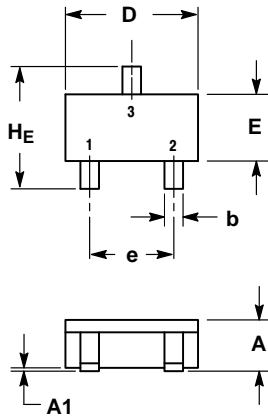


Figure 11. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

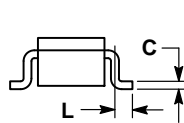
SC-59  
CASE 318D-04  
ISSUE H



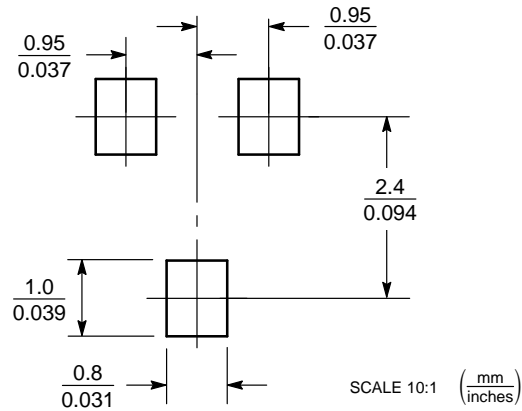
- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR



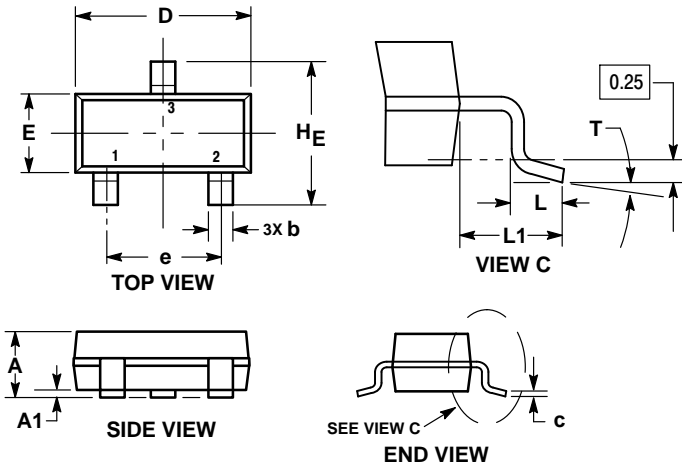
SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AR

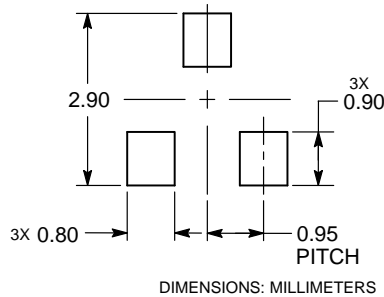


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

RECOMMENDED  
SOLDERING FOOTPRINT\*



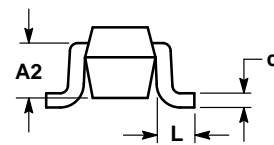
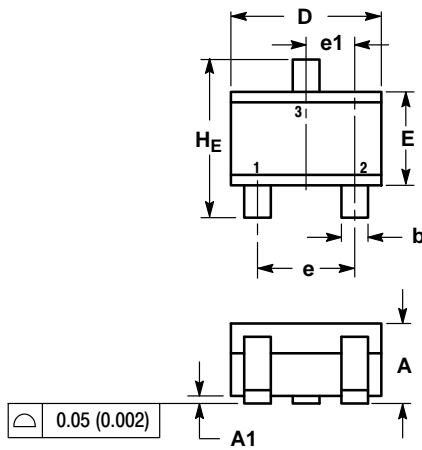
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



PACKAGE DIMENSIONS

SC-70 (SOT-323)  
CASE 419-04  
ISSUE N

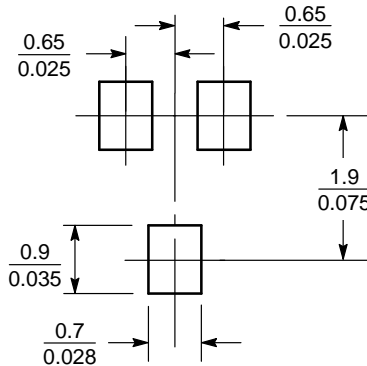
NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:  
PIN 1: BASE  
2: EMITTER  
3: COLLECTOR

SOLDERING FOOTPRINT\*

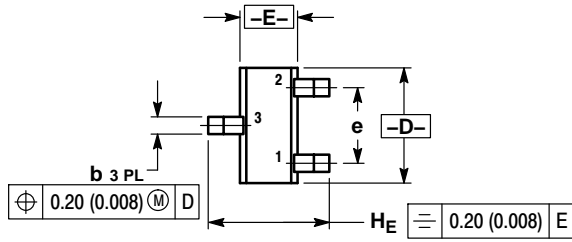


SCALE 10:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

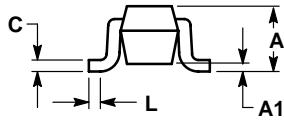
PACKAGE DIMENSIONS

SC-75/SOT-416  
CASE 463  
ISSUE G



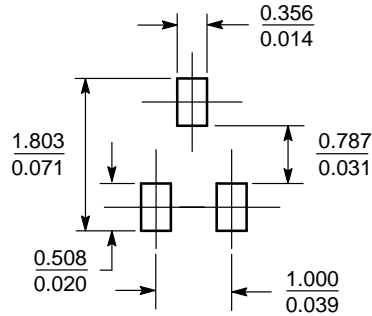
- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H <sub>E</sub>	1.50	1.60	1.70	0.060	0.063	0.067



- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

SOLDERING FOOTPRINT\*

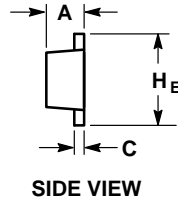
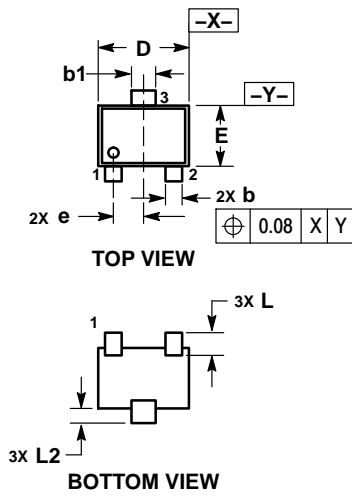


SCALE 10:1 ( $\frac{\text{mm}}{\text{inches}}$ )

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-723  
CASE 631AA  
ISSUE D

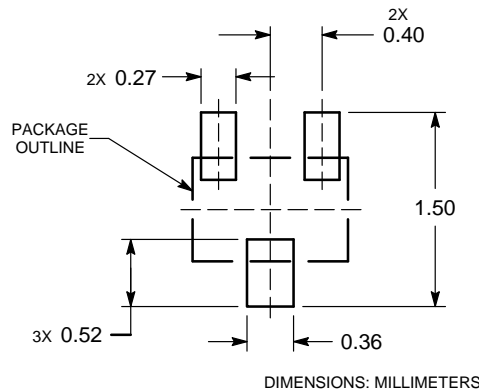


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H <sub>E</sub>	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

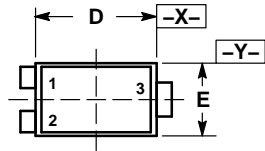
RECOMMENDED  
SOLDERING FOOTPRINT\*



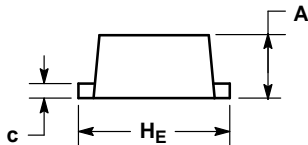
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

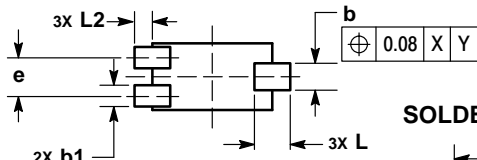
SOT-1123  
CASE 524AA  
ISSUE C



TOP VIEW

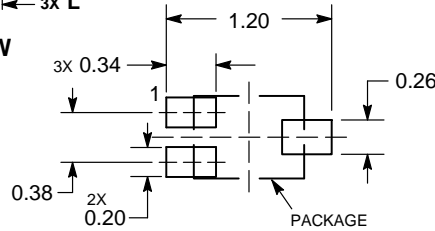


SIDE VIEW



BOTTOM VIEW

SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.34	0.40
b	0.15	0.28
b1	0.10	0.20
c	0.07	0.17
D	0.75	0.85
E	0.55	0.65
e	0.35	0.40
HE	0.95	1.05
L	0.185	REF
L2	0.05	0.15

STYLE 1:

1. BASE
2. EMITTER
3. COLLECTOR

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